BD810

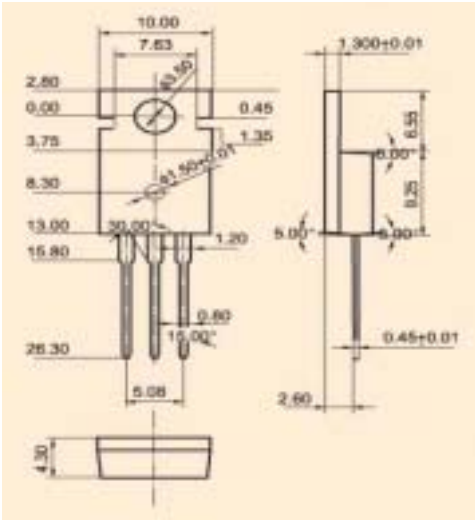
Silicon PNP Transistors



B C E

◆ Features

. Designed for use in high power audio amplifiers utilizing complementary or quasi complementary circuits.
. With TO-220 package



TO-220

◆ Absolute Maximum Ratings Tc=25℃

SYMBOL	PARAMETER	RATING	UNIT
V_{CBO}	Collector to base voltage	80	V
V_{CEO}	Collector to emitter voltage	80	V
V_{EBO}	Emitter to base voltage	5.0	V
I_B	Base collector current	6.0	A
I_C	Collector current	10	A
P_C	Collector power dissipation	90	W
T_j	Junction temperature	150	℃
T_{stg}	Storage temperature	-55~150	℃

◆ Electrical Characteristics Tc=25℃

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
I_{CBO}	Collector-base cut-off current	V_{CB}=80V; I_E=0			1.0	mA
I_{EBO}	Emitter-base cut-off current	V_{EB}=5.0V; I_C=0			2.0	mA
I_{CEO}	Collector-emitter cut-off current					
V_{CBO}	Collector-base breakdown voltage					
$V_{(BR)ceo}$	Collector-emitter breakdown voltage	I_C=0.1A; I_B=0	80			V
V_{EBO}	Emitter-base breakdown voltage					
$V_{CE(sat-1)}$	Collector-emitter saturation voltages	I_C=3A; I_B=0.3A			1.1	V
$V_{CE(sat-2)}$	Collector-emitter saturation voltages					
h_{FE-1}	Forward current transfer ratio	I_C=2A; V_{CE}=2V	30			
h_{FE-2}	Forward current transfer ratio	I_C=4A; V_{CE}=2V	15			
h_{FE-3}	Forward current transfer ratio					
$V_{BE(on)1}$	Base-emitter on voltages	I_C=4A; V_{CE}=2V			1.6	V
$V_{BE(on)2}$	Base-emitter on voltages					
f_T	Transition frepuency	V_{CE}=10V ;I_C=1A;f=1MHz	1.5			MHz
C_{ob}	Output Capacitance					